



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



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## Features

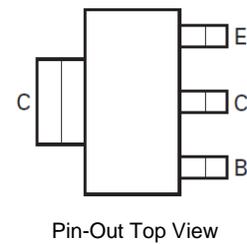
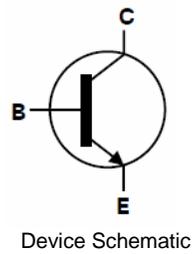
- $BV_{CEO} > 160V$
- $BV_{EBO} > 6V$
- $I_C = 600mA$  Continuous Collector Current
- Low Saturation Voltage (150mV max @10mA)
- $h_{FE}$  specified up to 50mA for a high gain hold up
- Complementary PNP Type: NK-DZT5401

## Mechanical Data

- Package: SOT223
- Package material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.112 grams (approximate)

## Applications

- High-voltage amplification applications
- High-voltage switching applications



### Maximum Ratings (@ $T_A = +25^{\circ}\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	160	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Continuous Collector Current	$I_C$	600	mA
Peak Collector Current	$I_{CM}$	1	A

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Leads (Note 6)	$R_{\theta JL}$	45	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	27	$^{\circ}\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^{\circ}\text{C}$

- Notes:
5. Device mounted on 50mm X 50mm X 1.6mm FR-4 PCB with high coverage of single sided 1 oz. copper, in still air condition
  6. Thermal resistance from junction to solder-point (at the end of the collector lead).
  7. Thermal resistance from junction to the top of the case.

## Thermal Characteristics and Derating Information

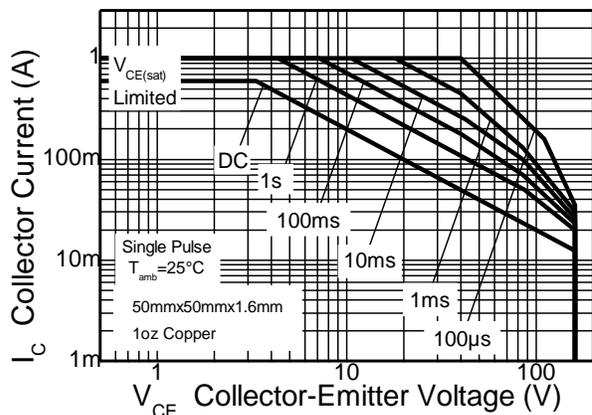


Figure 1. Safe Operating Area

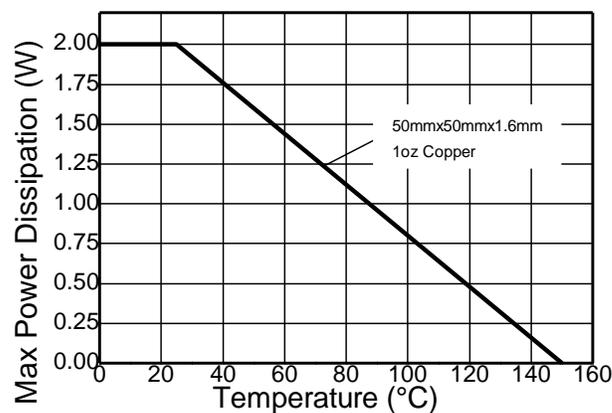


Figure 2. Derating Curve

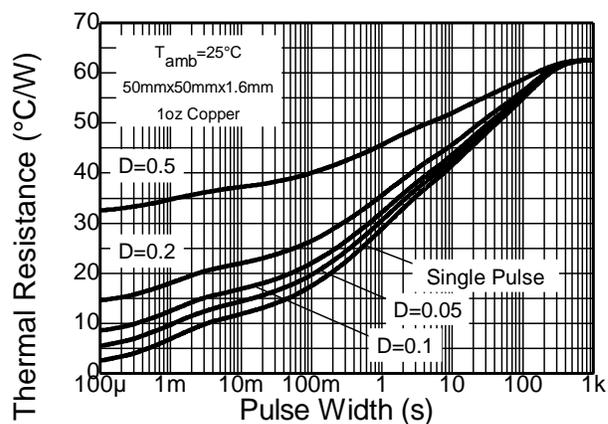


Figure 3. Transient Thermal Impedance

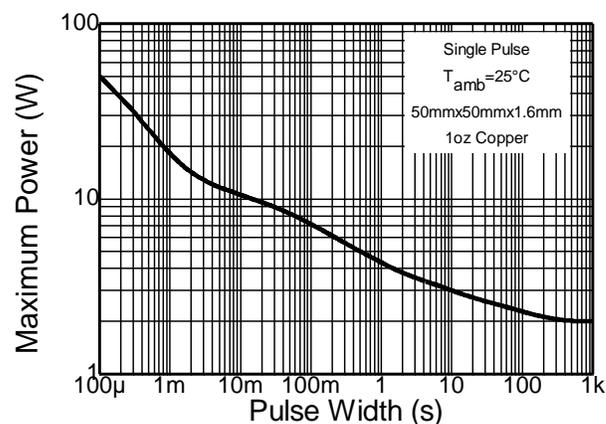


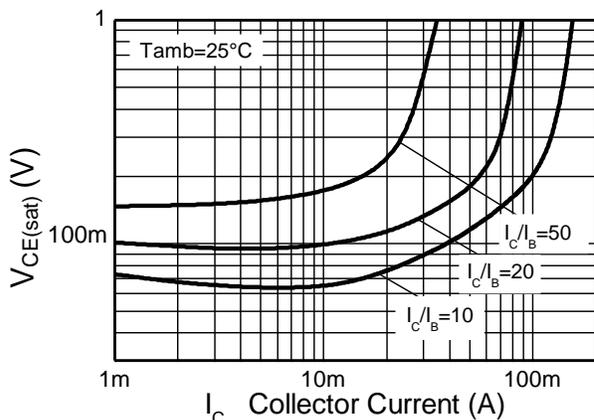
Figure 4. Pulse Power Dissipation

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

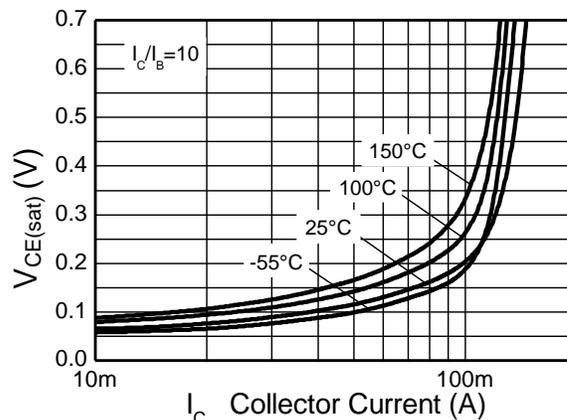
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	$BV_{CBO}$	180	270	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 8)	$BV_{CEO}$	160	200	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0	7.85	—	V	$I_E = 100\mu\text{A}$
Collector Cutoff Current	$I_{CBO}$	—	1	50	nA	$V_{CB} = 120\text{V}$
Emitter Cutoff Current	$I_{EBO}$	—	1	50	nA	$V_{CB} = 120\text{V}, T_A = +100^\circ\text{C}$
						$V_{EB} = 4\text{V}$
<b>ON CHARACTERISTICS (Note 8)</b>						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	65	150	mV	$I_C = 10\text{mA}, I_B = 1\text{mA}$
		—	115	200	mV	$I_C = 50\text{mA}, I_B = 5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	760	1000	mV	$I_C = 10\text{mA}, I_B = 1\text{mA}$
		—	840	1200	mV	$I_C = 50\text{mA}, I_B = 5\text{mA}$
DC Current Gain	$h_{FE}$	80	130	—	—	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$
		80	145	250	—	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$
		30	65	—	—	$I_C = 50\text{mA}, V_{CE} = 5\text{V}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	$f_T$	100	130	300	MHz	$V_{CE} = 10\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Small Signal Current Gain	$h_{fe}$	50	—	260	—	$V_{CE} = 10\text{V}, I_C = 10\text{mA}, f = 1\text{kHz}$
Output Capacitance	$C_{obo}$	—	—	6	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Noise Figure	NF	—	—	8	dB	$V_{CE} = 5.0\text{V}, I_C = 200\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$
Delay Time	$t_{(d)}$	—	95	—	ns	$V_{CC} = 10\text{V}, I_C = 10\text{mA}, I_{B1} = -I_{B2} = 1\text{mA}$
Rise Time	$t_{(r)}$	—	64	—	ns	
Storage Time	$t_{(s)}$	—	1256	—	ns	
Delay Time	$t_{(f)}$	—	140	—	ns	

 Notes: 8. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2.0\%$ .

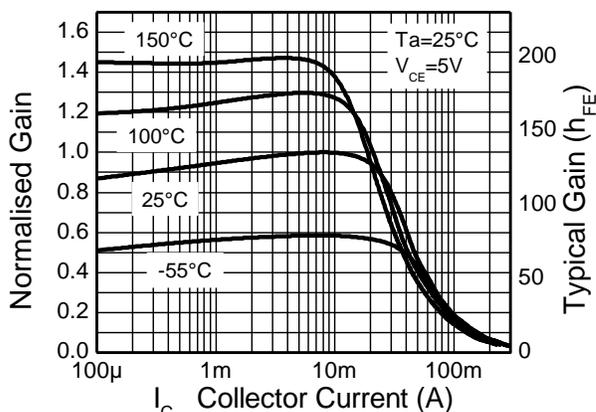
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



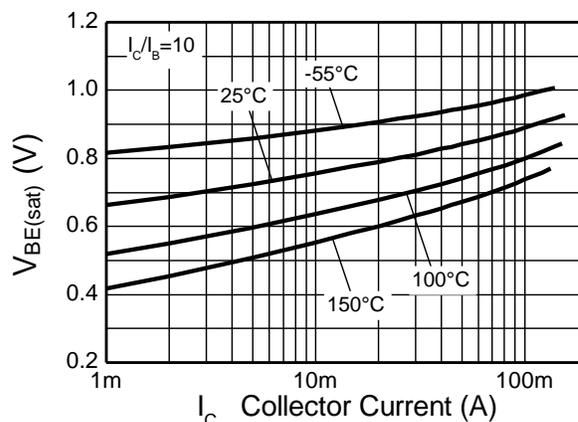
**Figure 5.  $V_{CE(sat)}$  v  $I_C$**



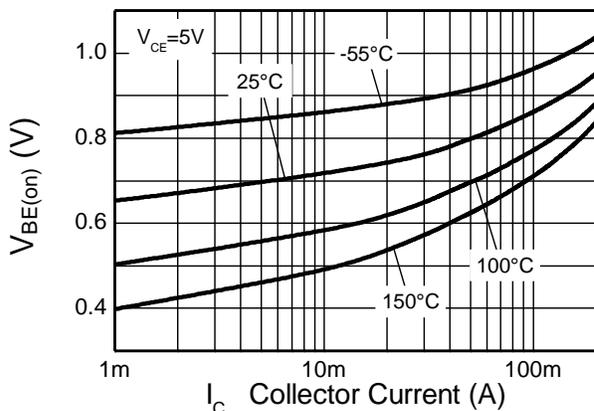
**Figure 6.  $V_{CE(sat)}$  v  $I_C$**



**Figure 7.  $h_{FE}$  v  $I_C$**



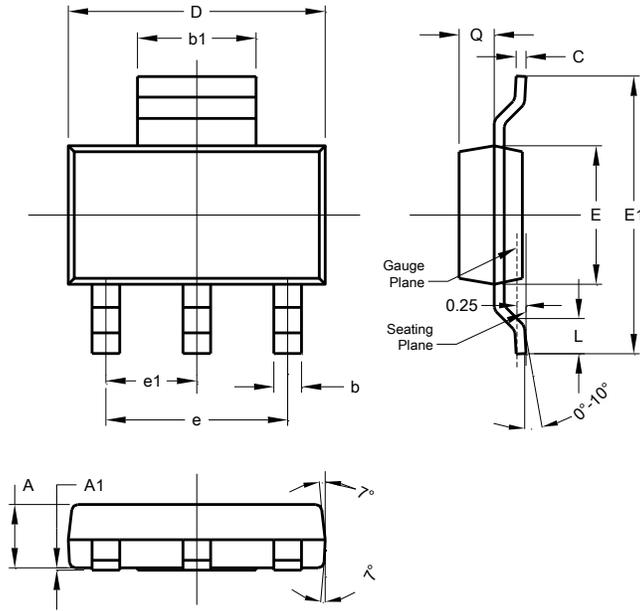
**Figure 8.  $V_{BE(sat)}$  v  $I_C$**



**Figure 9.  $V_{BE(on)}$  v  $I_C$**

## Package Outline Dimensions

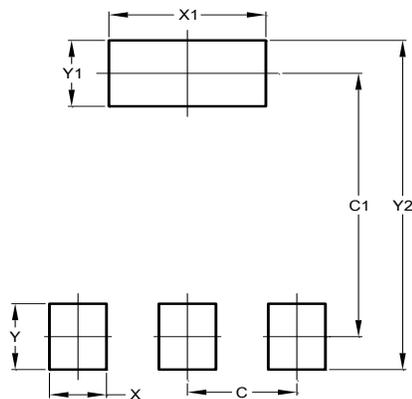
SOT223



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00